Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability of 1000 mW

3. Applications

- LED driver
- Power management
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	5.4	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 4.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	24	32	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u> </u>	D
2	S	source		
3	D	drain	1 2	G (i) 44)
			TO-236AB (SOT23)	S 017aaa253

6. Ordering information

Table 3. Ordering information

Type number	Package	e					
	Name	Description	Version				
PMV30UN2	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

7. Marking

Table 4. Marking codes

Table II III III II II II II II II II II II	
Type number	Marking code
	[1]
PMV30UN2	%K6

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	5.4	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	4.2	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	2.7	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	18	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	490	mW
			[1]	-	1000	mW
		$T_{sp} = 25 ^{\circ}C$		-	5000	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode		'	'	'	
I _S	source current	T _{amb} = 25 °C	[1]	-	0.9	Α

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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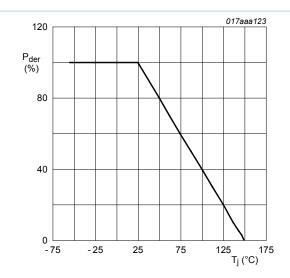


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times \textbf{100 \%}$$

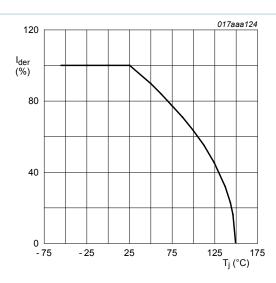


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

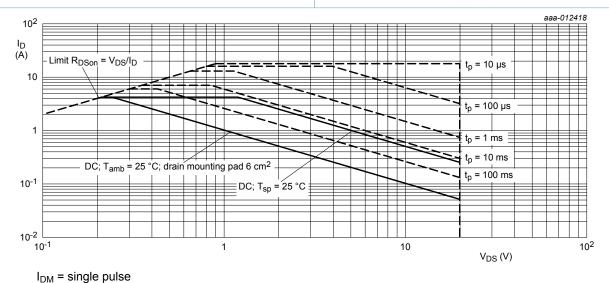


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	217	255	K/W
from junct ambient	from junction to		<u>[2]</u>	-	105	124	K/W
	ambient	t ≤ 5 s	<u>[2]</u>	-	73	86	K/W

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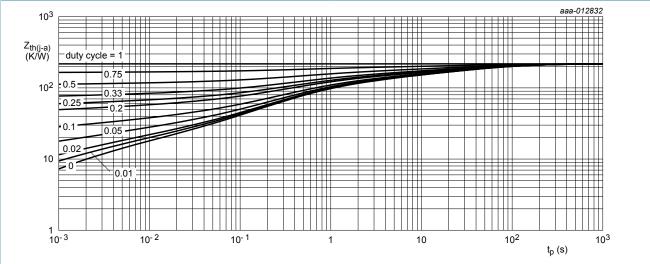
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	20	25	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

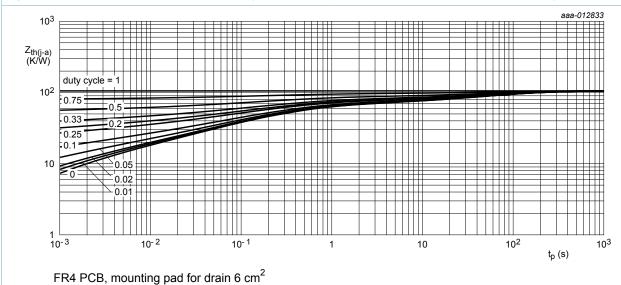


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, N-channel Trench MOSFET

10. Characteristics

Table 7 Characteristics

Table 7.	Characteristics		1			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 4.2 A; T _j = 25 °C	-	24	32	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 4.2 A; T _j = 150 °C	-	37	50	mΩ
		V _{GS} = 2.5 V; I _D = 3.7 A; T _j = 25 °C	-	30	43	mΩ
		V _{GS} = 1.8 V; I _D = 1.0 A; T _j = 25 °C	-	40	59	mΩ
		V _{GS} = 1.5 V; I _D = 0.1 A; T _j = 25 °C	-	56	100	mΩ
		V _{GS} = 1.2 V; I _D = 10 mA; T _j = 25 °C	-	160	-	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 2 A; T_{j} = 25 °C	-	15.8	-	S
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	-	7.6	-	Ω
Dynamic	characteristics		1			_
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 4.2 A; V_{GS} = 4.5 V;	-	6.2	11	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.8	-	nC
Q_{GD}	gate-drain charge		-	1.4	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	655	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	70	-	pF
C _{rss}	reverse transfer capacitance		-	62	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 10 V; I _D = 4.2 A; V _{GS} = 4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	26	-	ns
$t_{d(off)}$	turn-off delay time		-	35	-	ns
t _f	fall time		-	10	-	ns
Source-d	rain diode					_
V_{SD}	source-drain voltage	$I_S = 0.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.7	1.2	V

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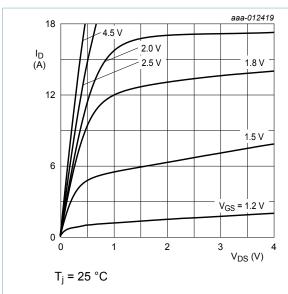


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

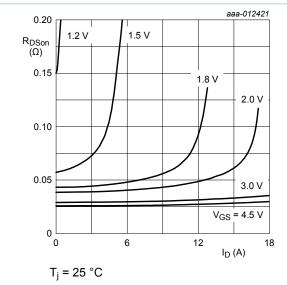


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

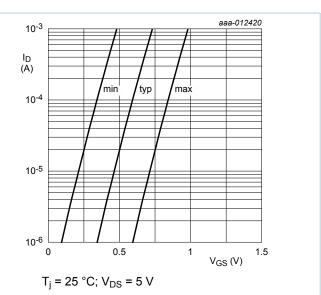


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

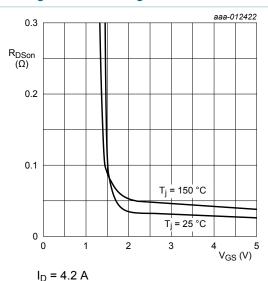


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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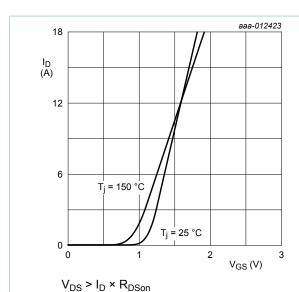


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

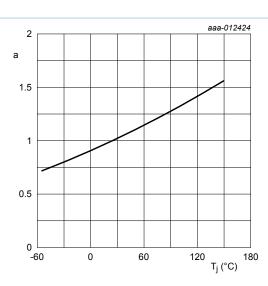


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

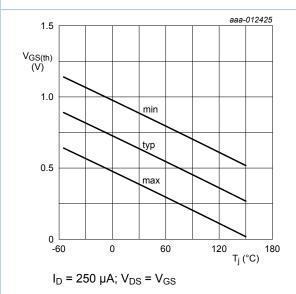


Fig. 12. Gate-source threshold voltage as a function of junction temperature

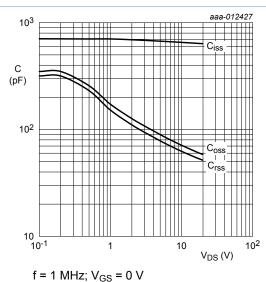


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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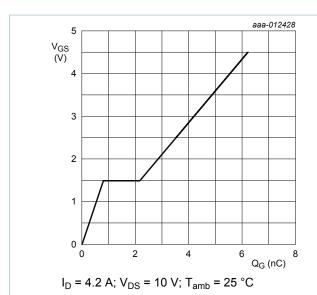


Fig. 14. Gate-source voltage as a function of gate charge; typical values

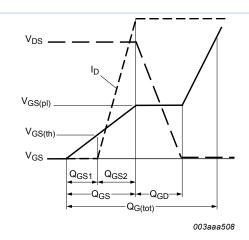


Fig. 15. MOSFET transistor: Gate charge waveform definitions

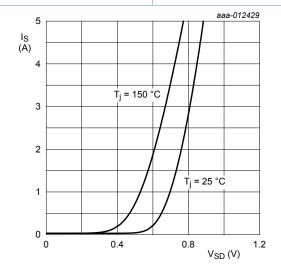
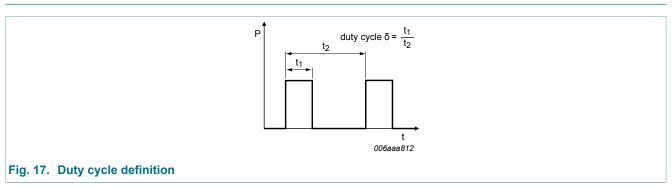


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



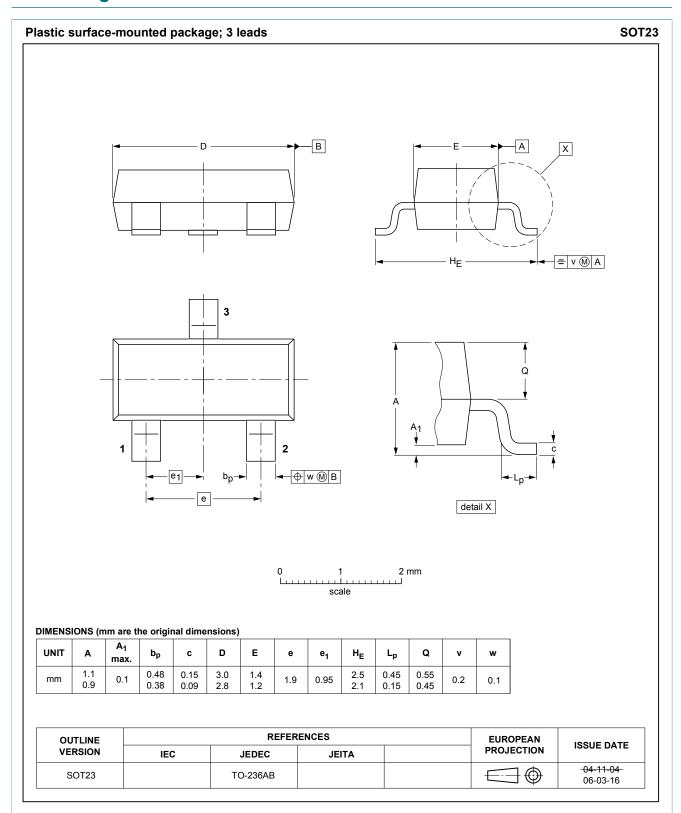
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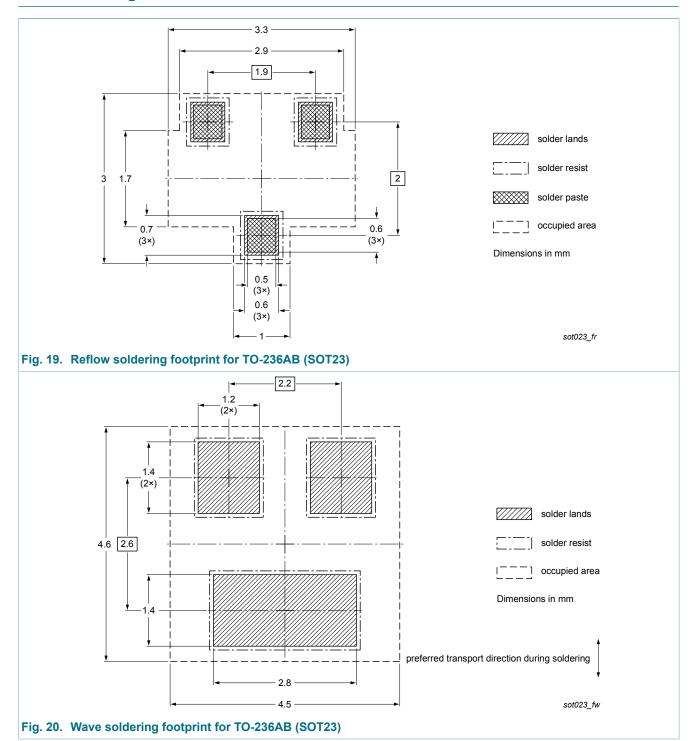
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV30UN2 v.1	20140424	Product data sheet	-	-

20 V, N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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